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| <b>Title of Change:</b>  | Qualification of Wafer Probe and Backside Process (BGBM) at ON Bucheon, Korea for Trench 2 and Trench 3 MOSFET Technology.   |   |
| <b>Proposed first ship date:</b>   | 1 June 2019  |   |
| <b>Contact information:</b>  | Contact your local ON Semiconductor Sales Office or <MohdHezri.AbuBakar@onsemi.com>  |   |
| <b>Samples:</b>  | Contact your local ON Semiconductor Sales Office or < <a href="mailto:PCN.samples@onsemi.com">PCN.samples@onsemi.com</a> ><br>Sample requests are to be submitted no later than 30 days from the date of first notification, Initial PCN or Final PCN, for this change.  |   |
| <b>Additional Reliability Data:</b>  | Contact your local ON Semiconductor Sales Office or <MohdAzizi.Azman@onsemi.com>   |   |
| <b>Type of notification:</b>   | This is a Final Product/Process Change Notification (FPCN) sent to customers. FPCNs are issued 90 days prior to implementation of the change.<br>ON Semiconductor will consider this change accepted, unless an inquiry is made in writing within 30 days of delivery of this notice. To do so, contact < <a href="mailto:PCN.Support@onsemi.com">PCN.Support@onsemi.com</a> >   |   |
| <b>Change Part Identification:</b>   | Affected parts will be identified with a date code of WW23'19 or later   |   |
| <b>Change Category:</b>  | <input checked="" type="checkbox"/> Wafer Fab Change <input type="checkbox"/> Assembly Change <input type="checkbox"/> Test Change <input type="checkbox"/> Other _____  |   |
| <b>Change Sub-Category(s):</b>   | <input checked="" type="checkbox"/> Manufacturing Site Addition <input type="checkbox"/> Material Change <input type="checkbox"/> Datasheet/Product Doc change<br><input type="checkbox"/> Manufacturing Site Transfer <input type="checkbox"/> Product specific change <input type="checkbox"/> Shipping/Packaging/Marking<br><input type="checkbox"/> Manufacturing Process Change <input type="checkbox"/> Other: _____ |   |
| <b>Sites Affected:</b>   | ON Semiconductor Sites:<br>ON Bucheon, Korea   | External Foundry/Subcon Sites:<br>None    |
| <b>Description and Purpose:</b>  |  |   |
| <p>This final change notification is to inform customers of ON Semiconductor's capacity expansion by qualifying an additional site of wafer probe and backside process (BGBM) for Trench (T2 &amp; T3) MOSFET technology at ON Bucheon, Korea. Current site of wafer probe and BGBM for T2 &amp; T3 MOSFET technology are located at ON Seremban and ON ISMF, Malaysia.</p> <p>Upon the expiration of this notification, all products listed here will have dual sites for wafer probe and BGBM.</p> <p>There are no product material change and no product marking change as a result of this change.</p> |  |   |
|  | <b>Before Change Description</b>   | <b>After Change Description</b>           |
| Wafer probe  | ON Seremban, Malaysia  | ON Seremban, Malaysia & ON Bucheon, Korea |
| BGBM   | ON ISMF, Malaysia  | ON ISMF, Malaysia & ON Bucheon, Korea     |



## Reliability Data Summary:

QV DEVICE NAME: NTMFS5832NLT1G

RMS: P47062

PACKAGE: SO8FL

| Test  | Specification                      | Condition                                  | Interval  | Results |
|-------|------------------------------------|--|-----------|---------|
| HTRB  | JESD22-A108                        | Ta=150°C, 80% max rated V                  | 1008 hrs  | 0/240   |
| HTGB  | JESD22-A108                        | Ta=150°C, 100% max rated Vgss              | 1008 hrs  | 0/240   |
| HTSL  | JESD22-A103                        | Ta= 150°C                                  | 2016 hrs  | 0/255   |
| IOL   | MIL-STD-750<br>(M1037)<br>AEC-Q101 | Ta=+25°C, delta Tj=100°C<br>On/off = 2 min | 15000 cyc | 0/240   |
| TC    | JESD22-A104                        | Ta= -55°C to +150°C                        | 1000 cyc  | 0/330   |
| HAST  | JESD22-A110                        | 130°C, 85% RH, 18.8psig, bias              | 192 hrs   | 0/240   |
| uHAST | JESD22-A118                        | 130°C, 85% RH, 18.8psig, unbiased          | 96 hrs    | 0/240   |
| PC    | J-STD-020 JESD-A113                | MSL 1 @ 260 °C                             |           | 0/1050  |

QV DEVICE NAME: NTMFS4931NT1G

RMS: S49203/S50996

PACKAGE: SO8FL

| Test  | Specification                      | Condition                                  | Interval  | Results |
|-------|------------------------------------|--|-----------|---------|
| HTRB  | JESD22-A108                        | Ta=150°C, 80% max rated V                  | 1008 hrs  | 0/251   |
| HTGB  | JESD22-A108                        | Ta=150°C, 100% max rated Vgss              | 1008 hrs  | 0/248   |
| HTSL  | JESD22-A103                        | Ta= 150°C                                  | 2016 hrs  | 0/247   |
| IOL   | MIL-STD-750<br>(M1037)<br>AEC-Q101 | Ta=+25°C, delta Tj=100°C<br>On/off = 2 min | 15000 cyc | 0/252   |
| TC    | JESD22-A104                        | Ta= -55°C to +150°C                        | 1000 cyc  | 0/238   |
| HAST  | JESD22-A110                        | 130°C, 85% RH, 18.8psig, bias              | 192 hrs   | 0/252   |
| uHAST | JESD22-A118                        | 130°C, 85% RH, 18.8psig, unbiased          | 96 hrs    | 0/252   |
| PC    | J-STD-020 JESD-A113                | MSL 1 @ 260 °C                             |           | 0/994   |
| RSH   | JESD22- B106                       | Ta = 265C, 10 sec                          |           | 0/90    |



**Electrical Characteristic Summary:**

Electrical characteristics are not impacted.

**List of Affected Parts:**

**Note:** Only the standard (off the shelf) part numbers are listed in the parts list. Any custom parts affected by this PCN are shown in the customer specific PCN addendum in the PCN email notification, or on the [PCN Customized Portal](#).

| Part Number        | Qualification Vehicle |
|--------------------|-----------------------|
| NTMFS4823NT1G      | NTMFS5832NLT1G        |
| NTMFS4823NT1G-IRH1 | NTMFS5832NLT1G        |
| NTMFS5832NLT1G     | NTMFS5832NLT1G        |
| NTMFS5844NLT1G     | NTMFS5832NLT1G        |
| NTTF55811NLTAG     | NTMFS5832NLT1G        |
| NTTF55820NLTAG     | NTMFS5832NLT1G        |
| NTTF55826NLTAG     | NTMFS5832NLT1G        |



**Table of Sites:** *This table is necessary for the proper functioning of the Change Category selection button. The whole table should be removed once the document has been prepared*

| ON Semiconductor Sites  | External Foundry/Subcon Sites  |
|---|--|
| None<br>All Sites<br>ON Oudenaarde, Belgium<br>ON ISMF, Malaysia<br>ON Burlington, Canada<br>ON Roznov, Czech Republic<br>ON Mechlen, Belgium<br>ON Seremban, Malaysia<br>ON Pocatello, Idaho<br>ON Santa Clara, CA<br>ON Leshan, China<br>ON Carmona, Philippines<br>ON Nampa, Idaho<br>ON Shenzhen, China<br>ON Suzhou, China<br>ON Tarlac City, Philippines<br>ON Cebu, Philippines<br>ON Bucheon, Korea<br>ON Rochester, New York<br>ON S. Portland, Maine<br>ON Mountain Top, PA<br>ON Gunma, Japan<br>ON Dong Nai Province, Vietnam<br>ON Gresham, Oregon<br>ON Niigata, Japan<br>ON Binh Duong Province, Vietnam<br>ON Bangkok, Thailand | None<br>All Sites<br>Ardentec<br>Advanced Interconnections Corp<br>Aizu Fujitsu, Japan<br>ASMC<br>LFoundry<br>Unisem<br>Amkor Phil 1<br>Amkor Korea<br>Amkor Malaysia<br>ASE Korea<br>ASE Chungli<br>ASE Shanghai<br>ASE Kunshan<br>UTAC<br>LiteOn Korea |